# Microwave Engineering 

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## Notes 17 S-Parameter Measurements



## $S$-parameters are typically measured, at microwave frequencies, with a network analyzer (NA).

These instruments have found wide, almost universal, application since the mid to late 1970's.

* Vector* network analyzer: Magnitudes and phases of the $S$ parameters are measured.
* Scalar network analyzer: Only the magnitudes of the $S$-parameters are measured.

Most NA's measure 2-port parameters. Some measure 4 and 6 ports.

[^0]
## $S$-Parameter Measurements (cont.)

A Vector Network Analyzer (VNA) is usually used to measure $S$ parameters.


## Note:

If there are more than 2 ports, we measure different pairs of ports separately with a 2-port VNA.

## S-Parameter Measurements (cont.)



## $S$-Parameter Measurements (cont.)

We want to measure


Error boxes contain effects of test cables, connectors, couplers,...


## S-Parameter Measurements (cont.)



$$
\left[\begin{array}{ll}
A & B \\
C & D
\end{array}\right]^{\text {MEAS }}=\left[\begin{array}{ll}
A & B \\
C & D
\end{array}\right]^{A}\left[\begin{array}{ll}
A & B \\
C & D
\end{array}\right]\left[\begin{array}{ll}
A & B \\
C & D
\end{array}\right]^{B}
$$

De-embedded $\downarrow$

$$
\left[\begin{array}{ll}
A & B \\
C & D
\end{array}\right]=\left(\left[\begin{array}{ll}
A & B \\
C & D
\end{array}\right]^{A}\right)^{-1}\left[\begin{array}{ll}
A & B \\
C & D
\end{array}\right]^{\mathrm{MEAS}}\left(\left[\begin{array}{ll}
A & B \\
C & D
\end{array}\right]^{B}\right)^{-1}
$$

## $S$-Parameter Measurements (cont.)



Measurement plane A plane $B$

Assume error boxes are reciprocal (symmetric matrices)

$$
\text { We need to "calibrate" to find }\left[S^{A}\right] \text { and }\left[S^{B}\right] \text {. }
$$

If $\left[S^{A}\right]$ and $\left[S^{B}\right]$ are known $\Rightarrow$ we can extract $[S]$ from measurements.

This is called "de-embedding".

## "Short, open, match" calibration procedure



These loads are connected to the end of the cable from the VNA.

$$
\begin{aligned}
& S_{11 s c}^{m}=S_{11}^{\alpha}-\frac{\left(S_{21}^{\alpha}\right)^{2}}{1+S_{22}^{\alpha}} \\
& S_{11}^{m}=S_{11}^{\alpha}+\frac{\left(S_{21}^{\alpha}\right)^{2}}{1-S_{22}^{\alpha}} \\
& S_{11}^{m}=S_{11}^{\alpha}
\end{aligned} \begin{array}{cc}
3 \text { measurements: } \\
\left(S_{11 s c}^{m}, S_{110 c}^{m}, S_{11_{\text {macse }}}^{m}\right)
\end{array} \quad \begin{gathered}
\text { Recall from Notes 16: } \\
\Gamma_{i n}=S_{11}+\frac{S_{21} S_{12} \Gamma_{L}}{1-\Gamma_{L} S_{22}} \\
3 \text { unknowns: } \\
\left(S_{11}^{\alpha}, S_{21}^{\alpha}, S_{22}^{\alpha}\right)
\end{gathered}
$$

## Calibration (cont.)

## "Thru-Reflect-Line (TRL)" calibration procedure

This is an improved calibration method that involves three types of connections:

1) The "thru" connection, in which port 1 is directly connected to port 2.
2) The "reflect" connection, in which a load with an (ideally) large (but not necessarily precisely known) reflection coefficient is connected.
3) The "line" connection, in which a length of matched transmission line (with an unknown length) is connected between ports 1 and 2.

The advantage of the TRL calibration is that is does not require precise short, open, and matched loads.

This method is discussed in the Pozar book (pp. 193-196).

## Discontinuities

* In microwave engineering, discontinuities are often represented by pi or tee networks.
* Sometimes the pi or tee network reduces to a singe series or shunt element.
* For waveguide systems, the TEN is used to represent the waveguide.


## Discontinuities: Rectangular Waveguide



Inductive iris or strip


Capacitive iris or strip

$\Rightarrow$


## Discontinuities: RWG (cont.)



## Discontinuities: Microstrip



## Note:

For a good equivalent circuit, the element values are fairly stable over a wide range of frequencies.

## Z-Parameter Extraction

Assume a reciprocal and symmetrical waveguide or transmission-line discontinuity.

## Examples



## Z-Parameter Extraction (cont.)



The $Z_{2}$ element is split in two:


## Z-Parameter Extraction (cont.)

Assume that we place a short or an open along the plane of symmetry.


## Z-Parameter Extraction (cont.)

The short or open can be realized by using odd-mode or even-mode excitation.


Even/odd-mode analysis is very useful in analyzing devices (e.g., using HFSS).

## Z-Parameter Extraction (cont.)



$$
Z_{L}^{\mathrm{SC}}=Z_{0}\left(\frac{1+S_{11}^{\mathrm{SC}}}{1-S_{11}^{\mathrm{SC}}}\right)
$$



Even mode voltage waves

$$
Z_{L}^{\mathrm{OC}}=Z_{0}\left(\frac{1+S_{11}^{\mathrm{OC}}}{1-S_{11}^{\mathrm{OC}}}\right)
$$

## Z-Parameter Extraction (cont.)



Hence we have:

$$
\begin{gathered}
Z_{1}=Z_{0}\left(\frac{1+S_{11}^{\mathrm{SC}}}{1-S_{11}^{\mathrm{SC}}}\right) \\
Z_{2}=\frac{1}{2}\left(Z_{0}\left(\frac{1+S_{11}^{\mathrm{OC}}}{1-S_{11}^{\mathrm{OC}}}\right)-Z_{0}\left(\frac{1+S_{11}^{\mathrm{SC}}}{1-S_{11}^{\mathrm{SC}}}\right)\right)
\end{gathered}
$$

## De-embeding of a Line Length

We wish the know the reflection coefficient of a 1-port device under test (DUT), but the DUT is not assessable directly - it has an extra length of transmission line connected to it (whose length may not be known).


Replace DUT with short circuit $\left(S_{11}^{\text {DUT }} \rightarrow-1\right) \Rightarrow S_{11}^{\mathrm{MEAS}, \mathrm{SC}}=-e^{-j 2 \beta L}=-1 / e^{+j 2 \beta L}$

$$
S_{11}^{\mathrm{DUT}}=S_{11}^{\mathrm{MEAS}, \mathrm{DUT}} e^{+j 2 \beta L} \quad \square \quad S_{11}^{\mathrm{DUT}}=S_{11}^{\mathrm{MEAS}, \mathrm{DUT}}\left(\frac{-1}{S_{11}^{\mathrm{MEAS}, \mathrm{SC}}}\right)
$$


[^0]:    * The $S$ parameters are really complex numbers, not vectors, but this is the customary name. There is an analogy between complex numbers and 2D vectors.

